

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2003-177537

(43)Date of publication of application : 27.06.2003

(51)Int.Cl.

G03F 7/039
C08F 12/14
H01L 21/027

(21)Application number : 2002-060583

(71)Applicant : FUJI PHOTO FILM CO LTD

(22)Date of filing : 06.03.2002

(72)Inventor : MIZUTANI KAZUYOSHI
YASUNAMI SHOICHIRO
SHIRAKAWA KOJI
TAKAHASHI AKIRA
FUJIMORI TORU

(30)Priority

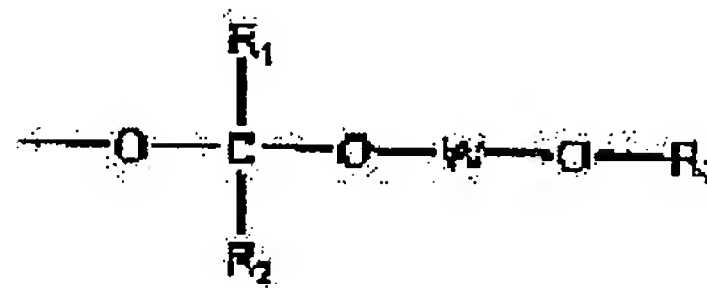
Priority number : 2001305364 Priority date : 01.10.2001 Priority country : JP

(54) POSITIVE RESIST COMPOSITION FOR ELECTRON BEAM, X-RAY OR EUV

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a positive resist composition which improves the profile of a resist pattern and suppresses a variation of line width due to laying in a vacuum chamber.

SOLUTION: The positive resist composition for an electron beam, X-rays or EUV (extreme-ultraviolet radiation) comprises (a) a resin which has a structural unit containing an acid-decomposable group of formula (X) and is decomposed by the action of an acid to increase solubility in an alkali developer and (b) a compound which generates an acid upon irradiation with an actinic radiation. In formula (X), R1 and R2 may be the same or different and are each H or a 1-4C alkyl; W is a divalent organic group; and R3 is an alkyl which may have substituents and has 11-20 carbon atoms in total, an aryl which may have substituents and has 11-30 carbon atoms in total or an aralkyl which may have substituents and has 12-30 carbon atoms in total.



50

LEGAL STATUS

[Date of request for examination] 14.05.2004

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]
[Patent number]
[Date of registration]
[Number of appeal against examiner's decision
of rejection]
[Date of requesting appeal against examiner's
decision of rejection]
[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office